

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	271	('power MOSFET' and 'epitaxial' and 'drift' and 'body' and 'dielectric')." .clm.."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/10 13:06
L2	211	('power MOSFET' and 'epitaxial' and 'drift' and 'body' and 'dielectric' and 'trenches')." .clm.."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/10 13:15
L3	6	('power MOSFET' and 'epitaxial' and 'drift' and 'body' and 'dielectric' and 'trenches').clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/10 13:15
S1	2	"20040070044"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/10 13:02
S2	4	((("6627949") or ("6593619"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/20 17:26
S3	1	"6184555".PN.	USPAT; USOCR	OR	ON	2004/11/20 17:27
S4	0	@ad<="20000602" and 'Power' with 'MOSFET' same 'low' with 'on resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:32
S5	373	@ad<="20000602" and 'MOSFET' same 'low' with 'on-resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 17:37
S6	288	@ad<="20000602" and 'MOSFET' same 'low' adj1 'on-resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 17:37
S7	236	@ad<="20000602" and 'MOSFET' with 'low' adj1 'on-resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 17:37
S8	111	@ad<="20000602" and 'high voltage' and 'MOSFET' with 'low' adj1 'on-resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 17:37

S9	141	@ad<="20000602" and 'high voltage' and 'MOSFET' with 'low' with 'on-resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 17:55
S10	92	@ad<="20000602" and 'high voltage' and 'MOSFET' and 'drift' and 'body' and 'trench'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/20 18:17
S11	62	@ad<="20000602" and 'high voltage' and 'MOSFET' and 'body regions' with 'trench'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:40
S12	3	("6441679").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 13:29
S13	2114	@ad<="20000602" and (327/538). ccls. or (323/282).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 10:13
S14	893	@ad<="20000602" and (327/538). ccls. or (323/282).ccls. and 'power MOSFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:35
S15	2	"20020070418"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:34
S16	1419	@ad<="20000602" and (257/496). ccls. or (257/491).ccls. or (257/E29. 26).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:39
S17	2	("6608350").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 13:37
S18	1	"6184555".PN.	USPAT; USOCR	OR	ON	2004/12/08 13:37
S19	1	"6103578".PN.	USPAT; USOCR	OR	ON	2004/12/08 13:38
S20	1	"4855804".PN.	USPAT; USOCR	OR	ON	2004/12/08 13:38

S21	1494	@ad<="20000602" and (257/341). CCLS. or (257/331).ccls. or (257/339).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:09
S22	137	@ad<="20000602" and 'power' with 'MOSFET' and 'body regions' with 'trench'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:58
S23	127	@ad<="20000602" and 'power MOSFET' and 'body regions' with 'trench'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:41
S24	441	@ad<="20000602" and 'International Rectifier' and 'High voltage'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:28
S25	71	@ad<="20000602" and 'International Rectifier' same 'High voltage'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 13:59
S26	70	@ad<="20000602" and 'trench' same 'deposit' same 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:22
S27	33	@ad<="20000602" and 'deposit' with 'trench' with 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:02
S28	2400	@ad<="20000602" and (438/268). CCLS. or (438/269).ccls. or (438/270-271).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:10
S29	474	@ad<="20000602" and (438/589). CCLS. or (438/44).ccls. or (438/245).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:11
S30	179	@ad<="20000602" and (438/360). CCLS. or (438/388).ccls. or (438/429).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:11
S32	2	("5250461").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 14:22

S33	224	@ad<="20000602" and 'epitaxial silicon' with 'trench'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:22
S34	264	@ad<="20000602" and 'International Rectifier' and 'High voltage' and 'MOSFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:32
S35	1	"6194773".PN.	USPAT; USOCR	OR	ON	2004/12/08 14:31
S36	1	"5549762".PN.	USPAT; USOCR	OR	ON	2004/12/08 14:31
S37	95	@ad<="20000602" and 'International Rectifier' and 'on-resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 14:33
S38	2	("6593619").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 15:07
S39	41	@ad<="20010504" and 'fill' with 'trench' with 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 09:22
S40	107	@ad<="20010504" and 'filled' with 'trench' same 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:40
S41	92	@ad<="20010504" and 'trench' with 'fill' same 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 09:48
S42	41	@ad<="20010504" and 'trench' with 'fill' with 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:41
S43	1	@ad<="20010504" and 'epitaxial silicon trench fill'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:41
S44	28	@ad<="20010504" and 'trench' with 'fill' same 'epitaxial' with 'dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 15:50

S45	3	@ad<="20000602" and 'trench' with 'epitaxial silicon' with 'liner'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 09:27
S46	9	@ad<="20000602" and 'liner' with 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 09:41
S47	9	@ad<="20000602" and 'trench' with 'P-type' with 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 09:42
S48	41	@ad<="20010504" and 'trench' with 'fill' with 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 14:24
S49	2	("6479352").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 10:13
S50	5600	@ad<="20000602" and (438/268). ccls. or (438/14).ccls. or (438/17). ccls. or (438/138).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 10:14
S51	1	"5973360".PN.	USPAT; USOCR	OR	ON	2004/12/09 10:15
S54	20	@ad<="20010504" and 'trench' with 'epitaxial silicon' and 'power' with 'MOSFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 14:25
S55	4	(("4473598") or ("4233091")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/02 13:09
S56	1	"6184555".PN.	USPAT; USOCR	OR	ON	2005/11/02 13:23
S57	1	"6103578".PN.	USPAT; USOCR	OR	ON	2005/11/02 13:25
S58	1	"4855804".PN.	USPAT; USOCR	OR	ON	2005/11/02 13:29
S59	1	"6184555".PN.	USPAT; USOCR	OR	ON	2005/11/02 13:29